

2N5338 AND 2N5339

5 AMP

HIGH SPEED NPN TRANSISTOR

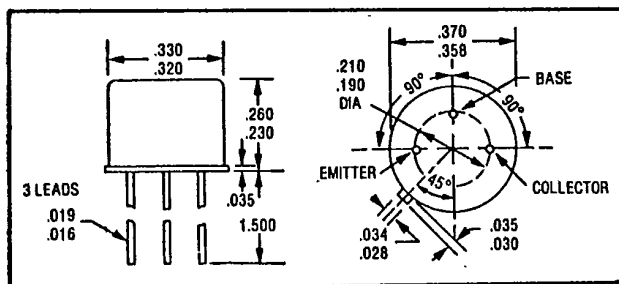
100 VOLTS



14830 Valley View Avenue
La Mirada, California 90638
(213) 921-9660
TWX 910-583-4807
FAX 213-921-2396

CASE STYLE W

JEDEC TO-5



FEATURES

- RADIATION TOLERANT
- FAST SWITCHING, 100 NSEC MAX t_d
- HIGH FREQUENCY, TYPICAL f_T 100 MHZ
- V_{CE0} 100 VOLTS MIN
- HIGH LINEAR GAIN, LOW SATURATION VOLTAGE
- 200°C OPERATING, GOLD EUTECTIC DIE ATTACH
- DESIGNED FOR COMPLEMENTARY USE WITH 2N6192 AND 2N6193
- 2N5334 THRU 2N5337 ALSO AVAILABLE

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CE0}	100	Volts
Collector - Base Voltage	V_{CB0}	100	Volts
Emitter - Base Voltage	V_{EB0}	6	Volts
Collector Current	I_C	5	Amps
Base Current	I_B	1	Amps
Total Device Dissipation @ $T_C = 25^\circ C$	P_D	6	Watts
Derate above $25^\circ C$		34.3	mW/°C
Operating and Storage Temperature	T_j, T_{stg}	-65 to +200	°C

THERMAL CHARACTERISTICS

Characteristics	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	29.2	°C/W

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector - Emitter Breakdown Voltage* ($I_C = 50$ mA dc)	BV_{CE0}^*	100		Vdc
Collector - Base Breakdown Voltage ($I_C = 200$ μ A dc)	BV_{CB0}	100		Vdc
Emitter - Base Breakdown Voltage ($I_E = 200$ μ A dc)	BV_{EB0}	6		Vdc

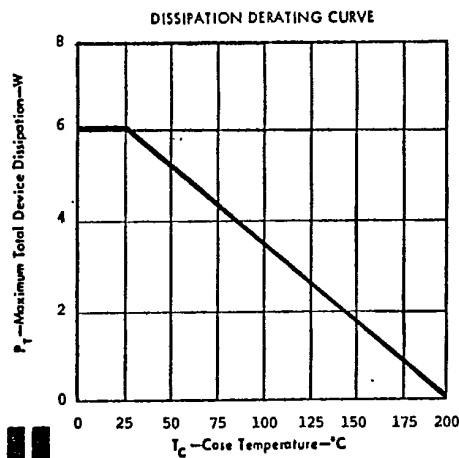
NOTE: All specifications subject to change without notice.

ELECTRICAL CHARACTERISTICS

Characteristics	Symbol	Min.	Max.	Unit
Collector Cutoff Current ($V_{CE} = 90 \text{ Vdc}$) ($V_{CE} = 90 \text{ Vdc}, V_{EB} = 1.5 \text{ Vdc}$) ($V_{CE} = 90 \text{ Vdc}, V_{EB} = 1.5 \text{ Vdc}, T_C = 150^\circ\text{C}$)			100 10 1.0	μAdc μAdc mAdc
Collector Cutoff Current ($V_{CB} = 100 \text{ Vdc}$)	I_{CBO}		10	μAdc
Emitter Cutoff Current ($V_{EB} = 6 \text{ Vdc}$)	I_{EBO}		100	μAdc
DC Current Gain* ($I_C = 500 \text{ mAdc}, V_{CE} = 2 \text{ Vdc}$) ($I_C = 2 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$) ($I_C = 5 \text{ Adc}, V_{CE} = 2 \text{ Vdc}$)	h_{FE}	30 60 30 60 20 40	120 240	
Collector - Emitter Saturation Voltage* ($I_C = 2 \text{ Adc}, I_B = 200 \text{ mAdc}$) ($I_C = 5 \text{ Adc}, I_B = 500 \text{ mAdc}$)	$V_{CE(SAT)}$		0.7 1.2	Vdc
Base - Emitter Saturation Voltage* ($I_C = 2 \text{ Adc}, I_B = 200 \text{ mAdc}$) ($I_C = 5 \text{ Adc}, I_B = 500 \text{ mAdc}$)	$V_{BE(SAT)}$		1.2 1.8	Vdc
Current - Gain - Bandwidth Product ($I_C = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, f = 10 \text{ MHz}$)	f_T	30		M Hz
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 100 \text{ KHz}$)	C_{ob}		250	pf
Input Capacitance ($V_{BE} = 2 \text{ Vdc}, I_C = 0, f = 100 \text{ KHz}$)	C_{ib}		1000	pf
Delay Time ($V_{CC} = 40 \text{ Vdc}$)	t_d		100	ns
Rise Time ($I_C = 2.0 \text{ Adc}$)	t_r		100	ns
Storage Time ($V_{EB}(\text{Off}) = 3.0 \text{ Vdc}$)	t_s		2.0	μs
Fall Time ($I_{B1} = I_{B2} = 200 \text{ mAdc}$)	t_f		200	ns

*Pulse Test: Pulse width = 300 μs , DutyCycle = 2%

TYPICAL OPERATING CURVES



FORWARD BIAS DC SAFE OPERATION AREA (S.O.A. CURVE)
CURVES APPLY BELOW RATED V_{CEO} $T_C = 25^\circ\text{C}$

